Analytical Simulation of L-I Characteristics for AR/HR Coated Double-Heterostructure AlGaAs/GaAs/AlGaAs Diode-Lasers Operating at 890 nm.

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Effect of Facet Reflectivities on High-power Highly Strained InGaAs Quantum-well Diode Lasers Operating at 1.2μm.


L-I Characteristics of AR–HR Coated AlGaAs LPE Grown Laser Diodes.